www.agelectronica.com

Silicon Diffused Power Transistor BU4530AW

GENERAL DESCRIPTION

Enhanced performance, new generation, high-voltage, high-speed switching npn transistor in a plastic envelope intended for use in horizontal deflection circuits of colour television receivers and p.c monitors. Features exceptional tolerance to base drive and collector current load variations resulting in a very low worst case dissipation.

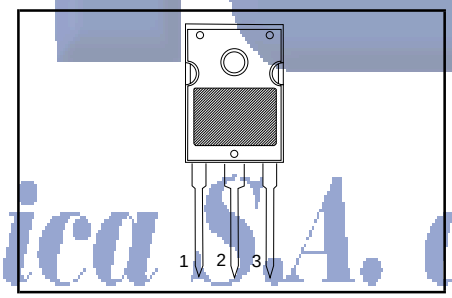
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	V_{BE} = 0	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	800	V
I_C	Collector current (DC)		-	16	A
I_{CM}	Collector current peak value		-	40	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25$ ˚C	-	125	W
V_{CEsat}	Collector-emitter saturation voltage	I_C = 10.0 A; I_B = 2.5 A	-	3.0	V
I_{Csat}	Collector saturation current	f = 32 kHz	10	-	A
		f = 90 kHz	8	-	A
t_f	Fall time	I_{Csat} = 10.0 A; f = 32 kHz	t.b.f	t.b.f	µs
		I_{Csat} = 8 A; f = 90 kHz	t.b.f	t.b.f	µs

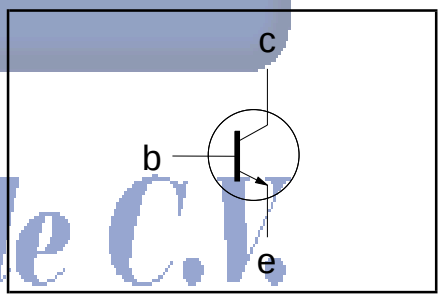
PINNING - SOT429

PIN	DESCRIPTION
1	base
2	collector
3	emitter
tab	collector

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	V_{BE} = 0 V	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	800	V
I_C	Collector current (DC)		-	16	A
I_{CM}	Collector current peak value		-	40	A
I_B	Base current (DC)		-	10	A
I_{BM}	Base current peak value		-	15	A
$-I_{BM}$	Reverse base current peak value [1]		-	10	A
P_{tot}	Total power dissipation	$T_{mb} \leq$ 25 ˚C	-	125	W
T_{stg}	Storage temperature		-55	150	˚C
T_j	Junction temperature		-	150	˚C

www.agelectronica.com